

SEMICONDUCTOR TECHNICAL DATA

KRC110S~

EPITAXIAL PLANAR NPN TRANSISTOR

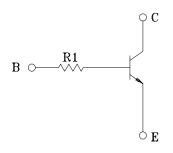
SWITCHING APPLICATION.

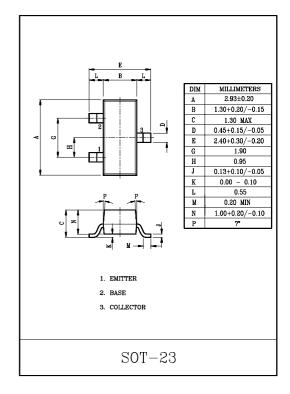
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- · With Built-in Bias Resistors.
- · Simplify Circuit Design.
- · Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT





MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	$V_{ ext{CEO}}$	50	V
Emitter-Base Voltage	$ m V_{EBO}$	5	V
Collector Current	$I_{\rm C}$	100	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	Pc	200	mW
Junction Temperature	T_{j}	150	Ç
Storage Temperature Range	$T_{\rm stg}$	-55 ~ 150	್ರೆ

ELECTRICAL CHARACTERISTICS (Ta=25°C)

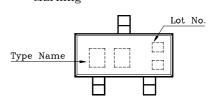
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=50V, I_{E}=0$	=	-	100	nA
Emitter Cut-off Current		$I_{ m EBO}$	V_{EB} =5 V , I_{C} =0	-	-	100	nA
DC Current Gain		$h_{ m FE}$	V _{CE} =5V, I _C =1mA	120	-	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =10mA, I _B =0.5mA	=	0.1	0.3	V
Transition Frequency		f _T *	V_{CE} =10V, I_{C} =5mA	-	250	_	MHz
	KRC110S	R_1		-	4.7	-	
	KRC111S			_	10	-	
Input Resistor	KRC112S			_	100	-	kΩ
	KRC113S			_	22	_	
	KRC114S			_	47	-	

Note: * Characteristic of Transistor Only

MARK SPEC

TYPE	KRC110S	KRC111S	KRC112S	KRC113S	KRC114S
MARK	NK	NM	NN	NO	NP

Marking



KRC110S~KRC114S

ELECTRICAL CHARACTERISTICS (Ta=25 $^{\circ}$ C)

СНА	RACTERIST	TIC	SYMBOL	TEST CONDITION	MIN.	ТҮР.	MAX.	UNIT
	Rise Time	KRC110S	t_{r}	V_{O} =5V V_{IN} =5V R_{L} =1k Ω	-	0.025	_	
		KRC111S			_	0.03	=	
		KRC112S			_	0.3	_	
		KRC113S			_	0.06	_	
		KRC114S			_	0.11		
	Storage Time	KRC110S	t _{stg}		_	3.0	_	
		KRC111S			_	2.0	-	
Switching Time		KRC112S			_	6.0	-	μS
		KRC113S			_	4.0	_	
		KRC114S			_	5.0	_	
		KRC110S	t _f		_	0.2	_	
		KRC111S			_	0.12	-	
		KRC112S			_	2.0	-	
		KRC113S			_	0.9	ı	
		KRC114S			_	1.4	-	